

Linear Systems replaces discontinued Siliconix JPAD200

The JPAD200 is a low leakage Pico-Amp Diode packaged in TO-92

The JPAD200 extremely low-leakage diode provides a superior alternative to conventional diode technology when reverse current (leakage) must be minimized. The JPAD200 features a leakage current of -200 pA and is well suited for use in applications such as input protection for operational amplifiers.

JPAD200 Benefits:

- Negligible Circuit Leakage Contribution
- Circuit "Transparent" Except to Shunt High-Frequency Spikes
- Simplicity of Operation

JPAD200 Applications:

- Op Amp Input Protection
- Multiplexer Overvoltage Protection

FEATURES

DIRECT REPLACEMENT FOR SILICONIX JPAD200

REVERSE BREAKDOWN VOLTAGE	$BV_R \geq -35V$
ULTRALOW LEAKAGE	$\leq 200 \text{ pA}$
REVERSE CAPACITANCE	$C_{RSS} \leq 2.0\text{pF}$

ABSOLUTE MAXIMUM RATINGS

@ 25°C (unless otherwise noted)

Maximum Temperatures

Storage Temperature	-65°C to +150°C
Operating Junction Temperature	-55°C to +135°C

Maximum Power Dissipation

Continuous Power Dissipation	350mW
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MAXIMUM CURRENT

Forward Current (Note 1)	10mA
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JPAD200 ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise noted)

SYMBOL	CHARACTERISTICS	MIN.	TYP.	MAX.	UNITS	CONDITIONS
BV_R	Reverse Breakdown Voltage	-35	--	--	V	$I_R = -1\mu A$
V_F	Forward Voltage	--	0.8	1.5	V	$I_F = 5\text{mA}$
C_{RSS}	Total Reverse Capacitance	--	1.5	2	pF	$V_R = -5V, f = 1\text{MHz}$
I_R	Maximum Reverse Leakage Current	--	--	-200	pA	$V_R = -20V$

Notes:

1. Absolute maximum ratings are limiting values above which JPAD200 serviceability may be impaired.

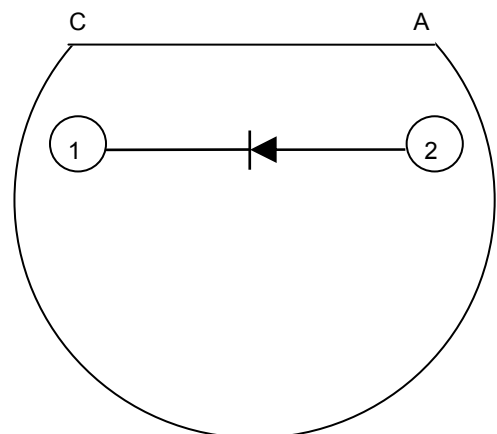
Available Packages:

JPAD200 in TO-92
JPAD200 available as bare die

Please contact Micross for full package and die dimensions



TO-92 (Bottom View)



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